NSN 5961-01-350-1244

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-350-1244 **Inclosure Material:** Metal **Overall Length:** 0.013 inches **Overall Height:** Between 0.005 inches and 0.008 inches Overall Width: 0.013 inches **Function For Which Designed:** Switching **Mounting Method:** Press fit **Features Provided:** Mounting pad **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 100.0 breakdown voltage, dc **Current Rating Per Characteristic:** 10.00 microamperes forward current, average peak **Power Rating Per Characteristic:** 200.0 milliwatts small-signal input power, common-collector **Capacitance Rating In Picofarads:** 0.1 **Maximum Operating Tempurature Per Measurement Point:** 85.0 degrees celsius ambient air **Special Features:** The diode shall be capable of fulfilling all requirements when attached to gold plated aluminum using a silver filled conductive epoxy; junction pattern arrangement: pn **Precious Material And Location:** Terminal surfaces gold **Precious Material:** Gold **Terminal Type And Quantity:** 1 bonding pad Shelf Life: N/a **Unit Of Measure: Demilitarization:**

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No